

Industrial Roll to Roll fabrication of PV and LOW-E thin films



Web Coating and Handling Conference

The Premier Event for Web Processing, Handling, and Finishing

2016 Europe
Dresden, Germany

INDUSTRIAL ROLL TO ROLL
fabrication of PV and LOW-E
thin films

S. Kreher

Agenda

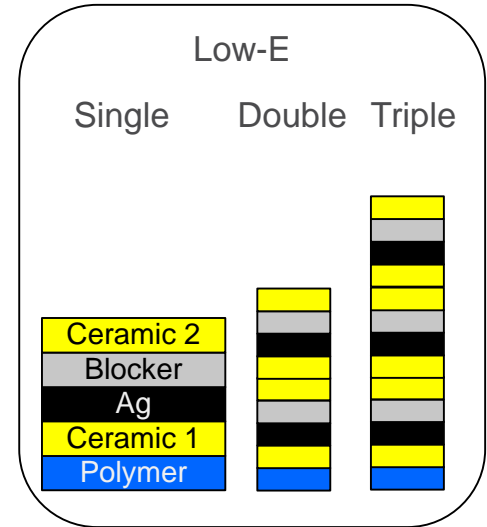
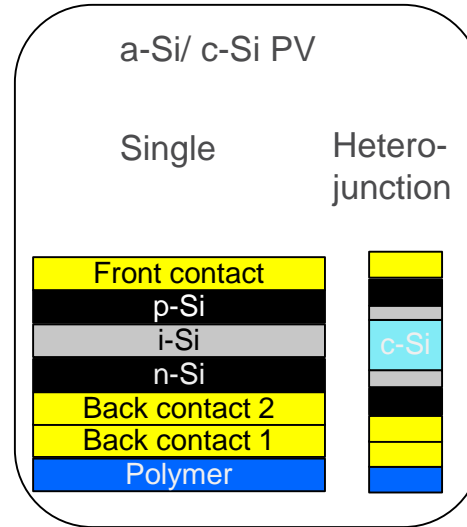
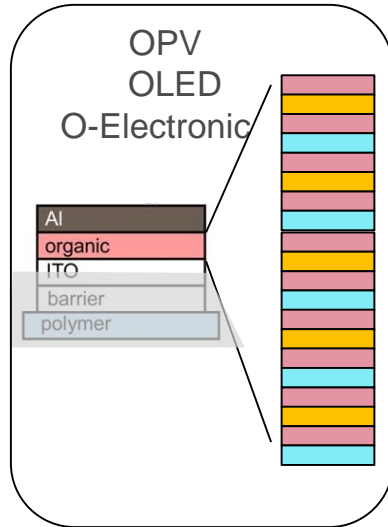
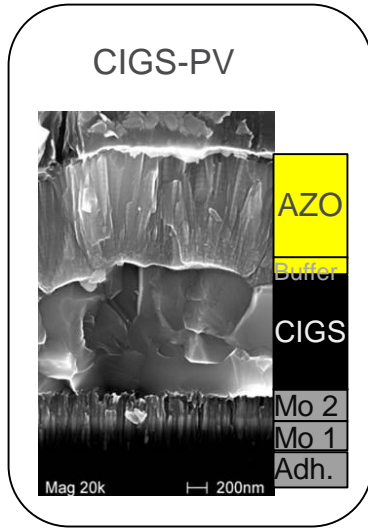
- ▴ Layer stacks and process demands
- ▴ Process/ drum concepts - Temperature Control
- ▴ Gas separation - Setups and corresponding gas separation factors
- ▴ Results

Layerstacks and process demands

Temperature and gas separation

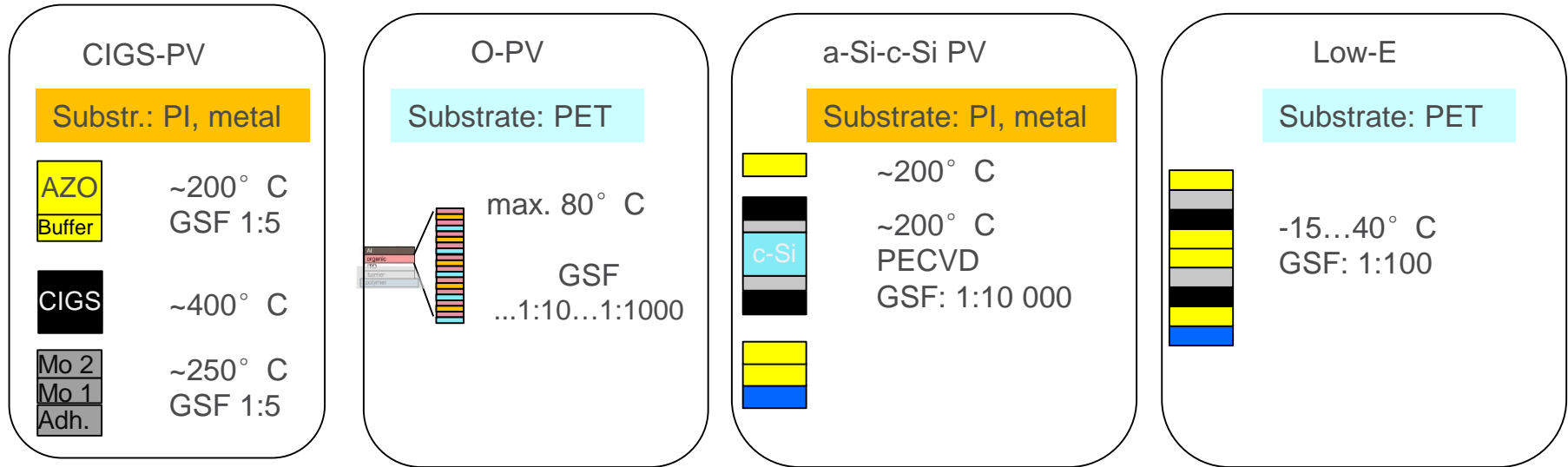
Layer stacks

Applications and layer stacks



Layer stacks

▲ Substrates, process temperatures and gas separation factor [GSF]



Industrial Roll to Roll fabrication of PV and LOW-E thin films



Process/ drum concepts

Temperature control

Process/ drum concepts

▲ Drum setups

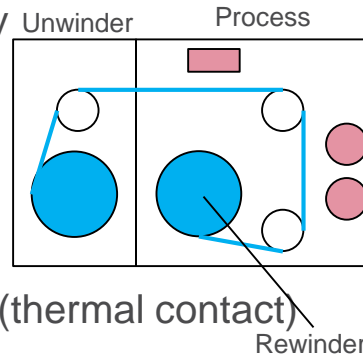
▲ Free span

no temperature control of web,
defined by radiation properties
surface, surrounding geometry
hot, robust processes,
PI-Web, metal substrate

Free Span, e.g.
FHR.Roll.300.PECVD
FHR.Roll.1000

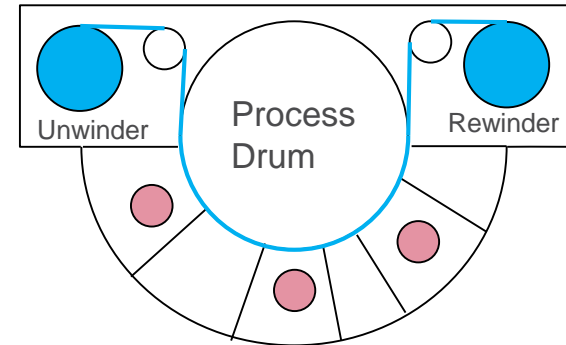
▲ Process Drum

(temperature controlled)
efficient for plastic foils
limited usability for metal foils (thermal contact)



Process Drum

Cool: -15...80° C PET foil
Warm: up to 300° C PI-foil
Hot: up to 600° C



Process/ drum concepts

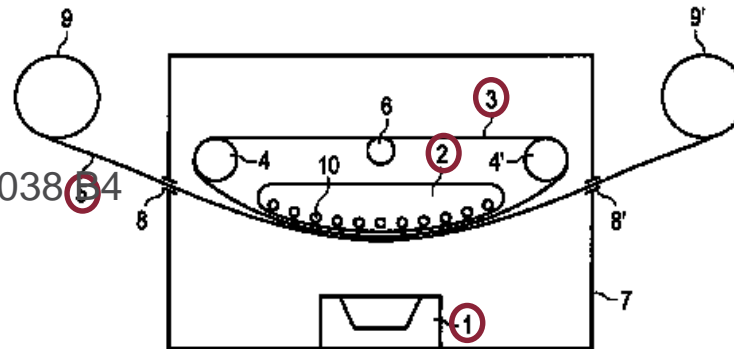
- ▲ Avoiding front contact of web and the need of large number or long deposition/ process zones for temperature controlled web would need large drum diameter e.g. >8m

- ▲ Solution:

- ▲ Metal belt drive

Patent DE 102009058038

- ▲ Virtual drum

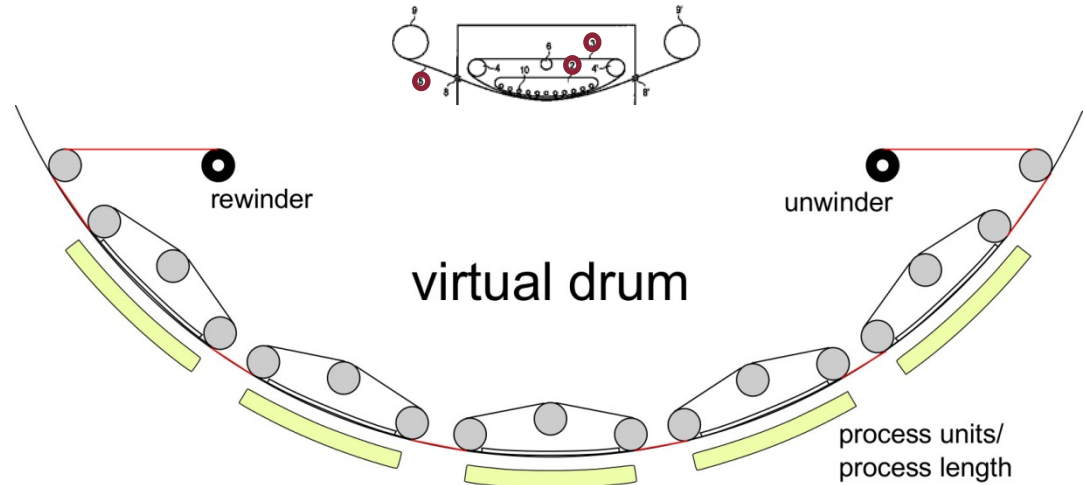


- (1) Evaporator
- (2) Temperature controlled unit
- (3) Metal belt (driven synchronously)
- (4) Drums
- (5) R2R Substrate
- (6) Band tension drum
- (7) Vacuum chamber
- (8) Valve/slit
- (9) Unwinder/re-winder
- (10) Tubings for temperature fluid

Industrial Roll to Roll fabrication of PV and LOW-E thin films

Process/ drum concepts

- ▲ Drum setups
- ▲ Metal belt drive
patent DE 102009058038 B4
- ▲ Virtual drum
- ▲ No front contact
- ▲ Theoretic diameter >10 m



Gas Separation

Setups and corresponding gas
separation factors

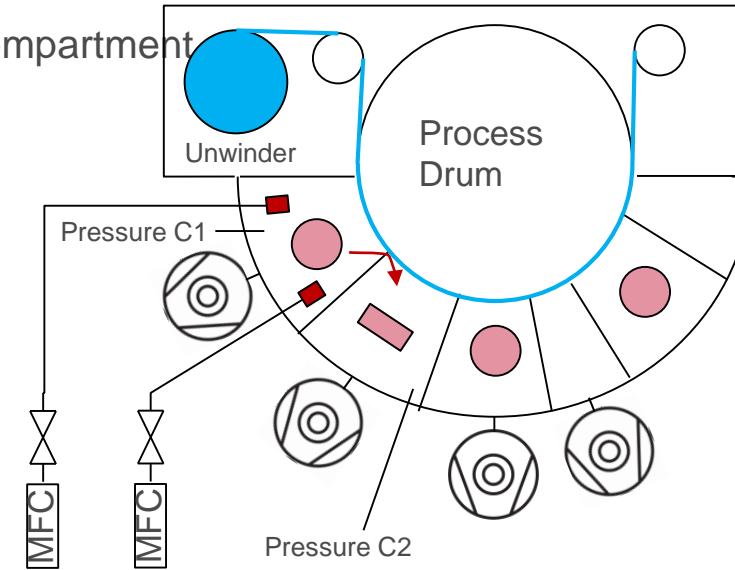
Gas Separation

- Intention: No gas contamination from adjacent process compartment

$$GSF = \frac{(\Delta)p_{SC1}}{(\Delta)p_{SC2}(-p_{baseSC2})}$$

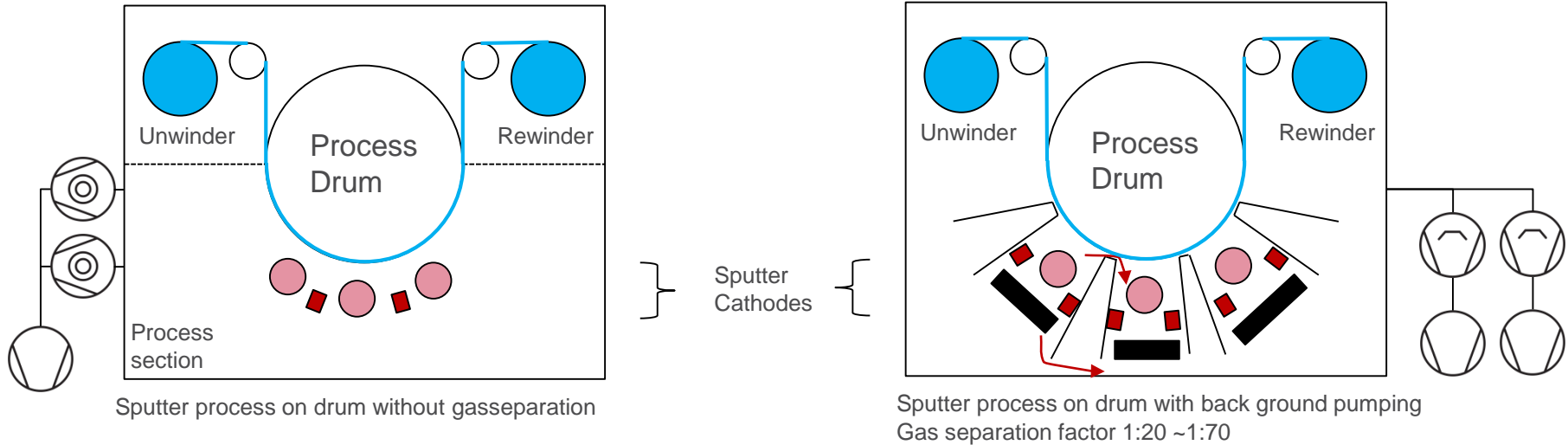
- Measurement
gas inlet in SC1
measure pressure (rise) in SC2

$(\Delta)p_{SC1}$... Pressure of compartment with active gas inlet
 $(\Delta)p_{SC2}$... Pressure of adjacent compartment with no gas inlet
 $p_{baseSC2}$... Base pressure of adjacent compartment with no gas inlet



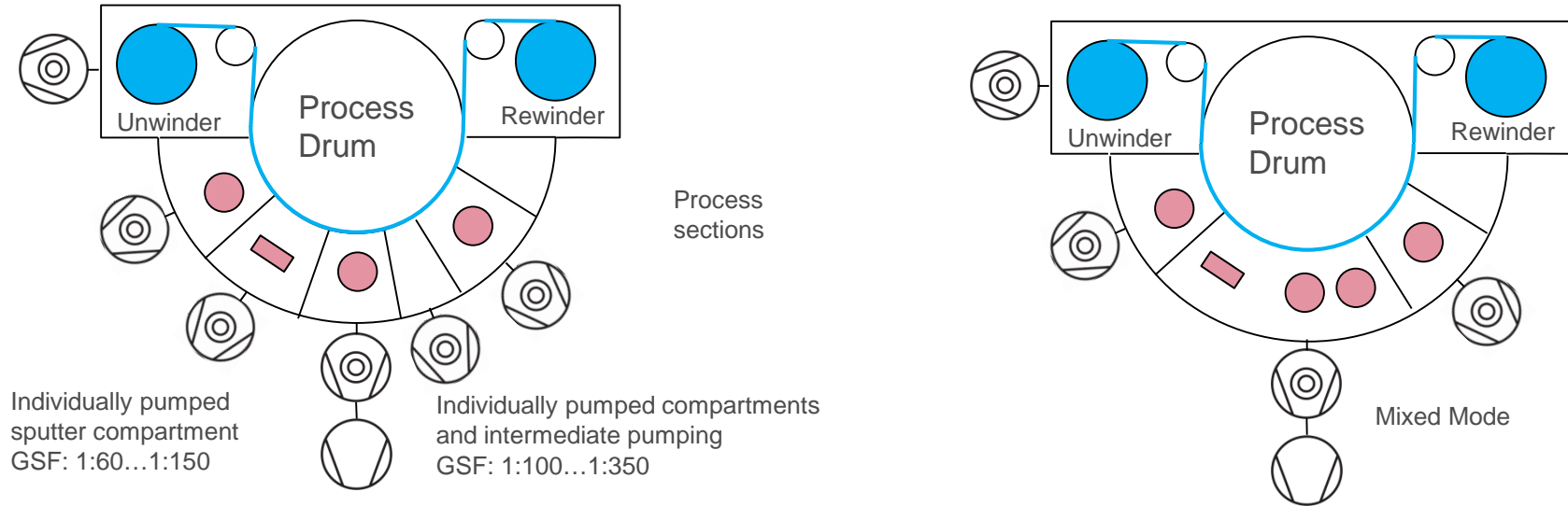
Gas Separation

▲ Gas separation factor[GSF]



Gas Separation

▲ Substrates, process temperatures and gas separation factor[GSF]



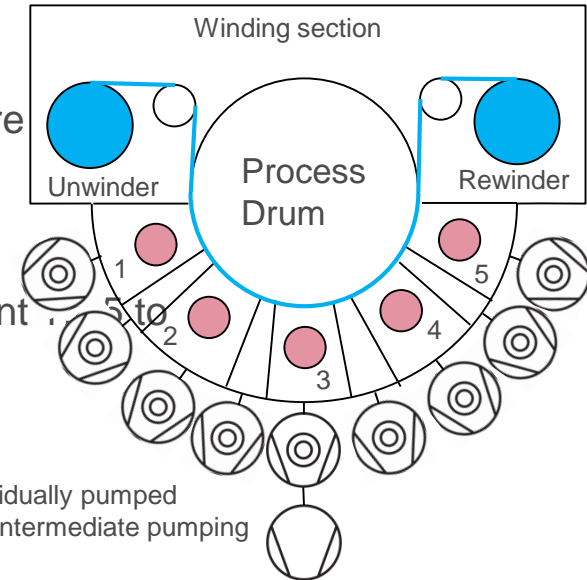
Gas Separation

- ▲ Gas separation factor [GSF]
- ▲ Thin metallic layers e.g. Ag react with oxygen partial pressure => high Gas Separation Factor is needed

$$GSF = \frac{(\Delta)p_{SC1}}{(\Delta)p_{SC2}(-p_{baseSC2})}$$

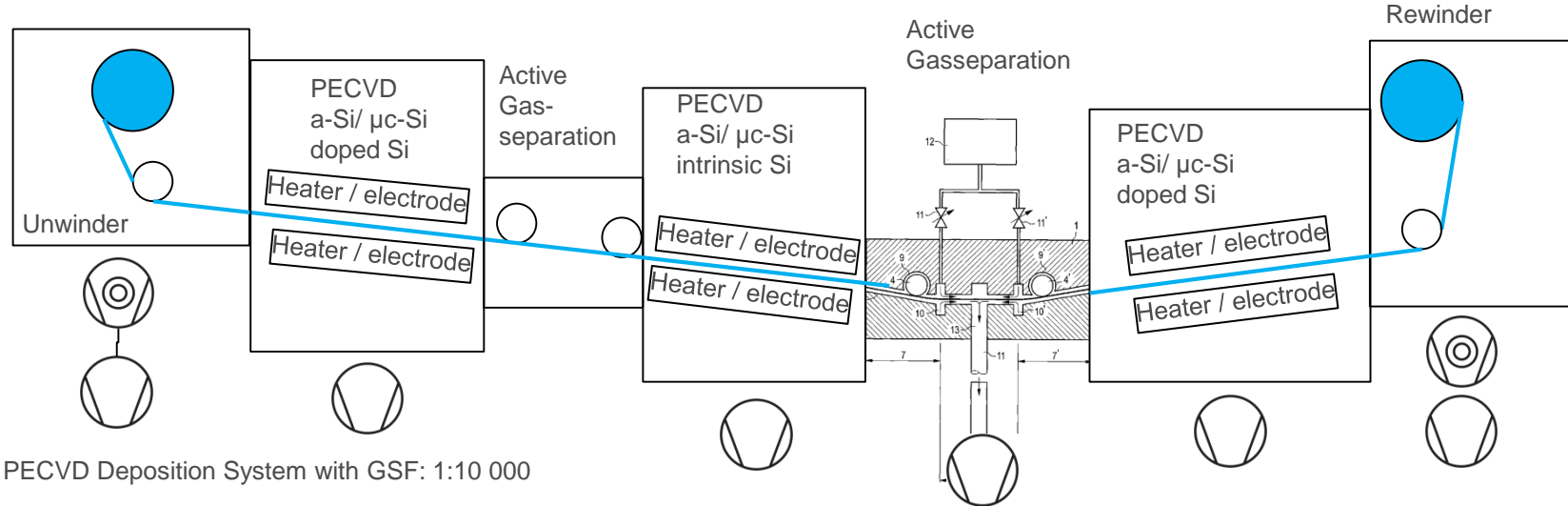
- ▲ Results: Measured Gas Separation Factors from compartment 1 to compartment 5 (critical / sensitiv material e.g. Silver)

Gas separation factor	Comp 1	Comp 2	Comp 3	Comp 4	Comp 5
Compartment 3 Ag	1575	399	-	250	1500



Gas Separation

- ▲ Ultra high gas separation between intrinsic Silicon and doped Silicon necessary



PECVD Deposition System with GSF: 1:10 000

Patented EP000002312014B1

Gas Separation

▲ GSF in PECVD-System:

- ▲ Process pressure ~ 1 mbar / torr / 100 Pa range
- ▲ High GSF needed between doping and intrinsic chambers
- => Doping of Si in the order 1:1E7...1:1E4
- ▲ no pressure rise measurement possible

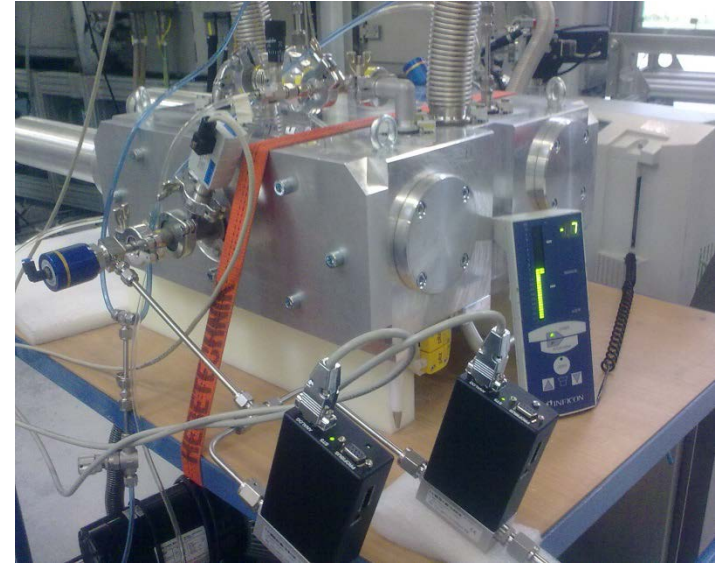
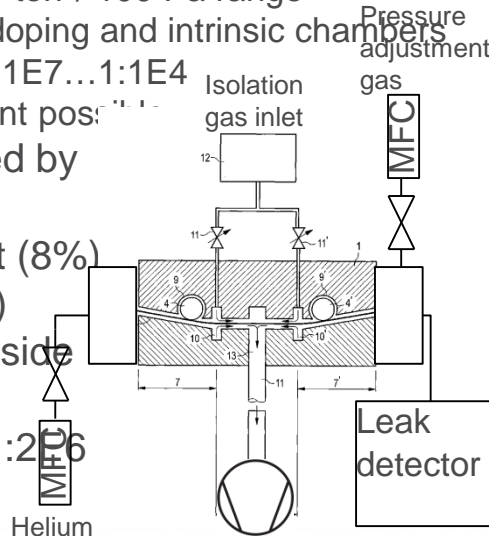
▲ Gas separation to be measured by He-“Leakage rate“ method:

100sccm N₂+ 14sccm He inlet (8%)
(simulating molecule behavior)
and leak detector on opposite side

$1E-7\text{mbar}\cdot\text{l/s}=6,6E-6\text{sccm}$

$14\text{sccm}:6,6E-6\text{sccm} \Rightarrow \text{GSF} = 1:2\ 000\ 000$

=> 1:2 000 000

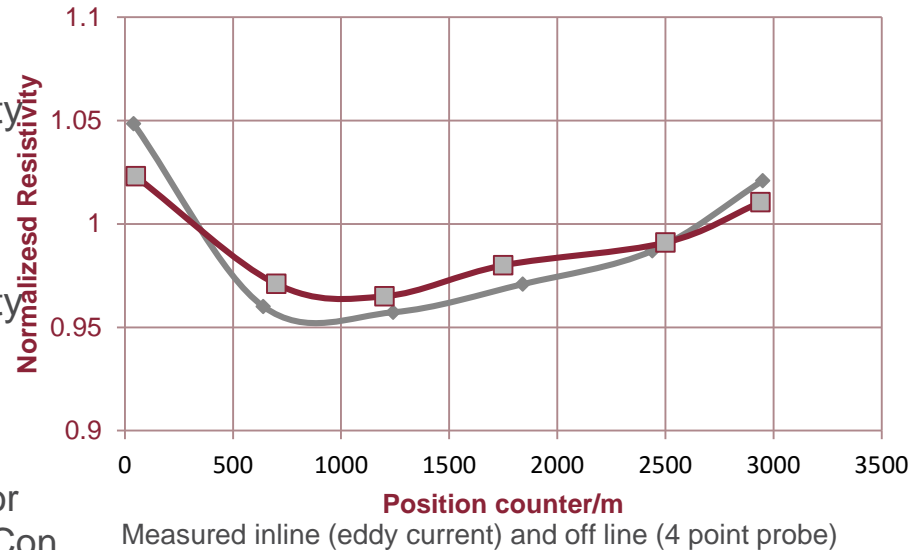


Patented EP000002312014B1

Results

Results - Production stability

- ▲ TCO e.g. for PV Application, Touch panel
- ▲ TCO down web resistivity +-5% nonuniformity
Constant process Parameters
Gray curve [1]
- ▲ TCO down web resistivity +-3% nonuniformity
with runtime dependent parameter change
Red curve



[1] S. Kreher, Dr. S.M. Van Eek, ITO processes for display and touch panel applications - SVC TechCon Proceedings (2016)

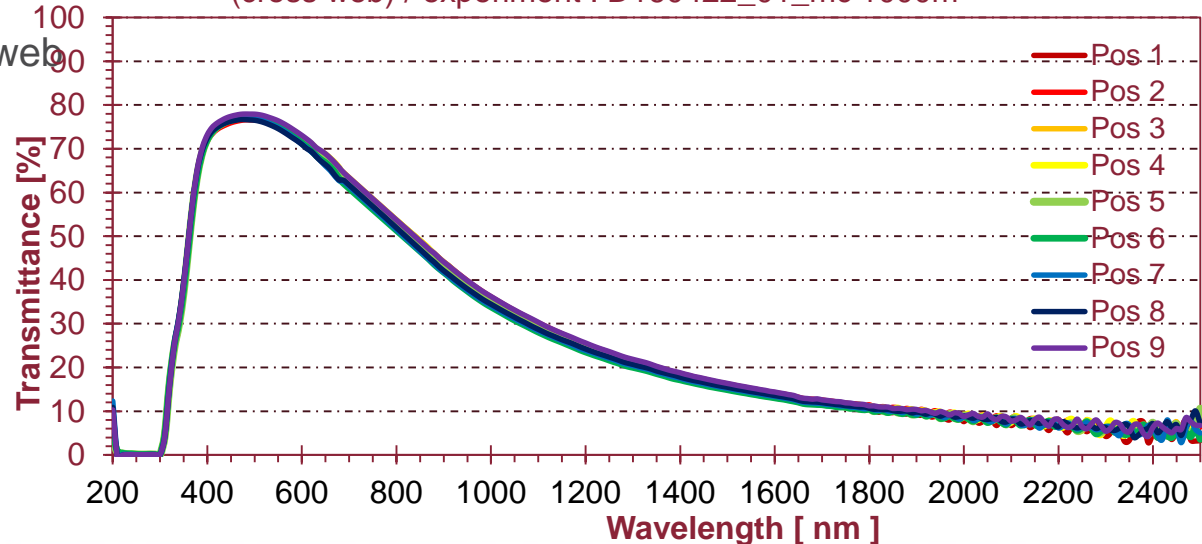
FHR Anlagenbau GmbH / www.fhr.de

Results - Production stability

- ▲ Results Low Emmissivity coatings
- ▲ Opt. transmittance cross web
- ▲ 9 measurement positions
- ▲ 1600mm width
- ▲ Single Ag Low-E

Transmittance Test-Low-E-Layerstack

(cross web) / experiment : D160422_01_mc 1000m

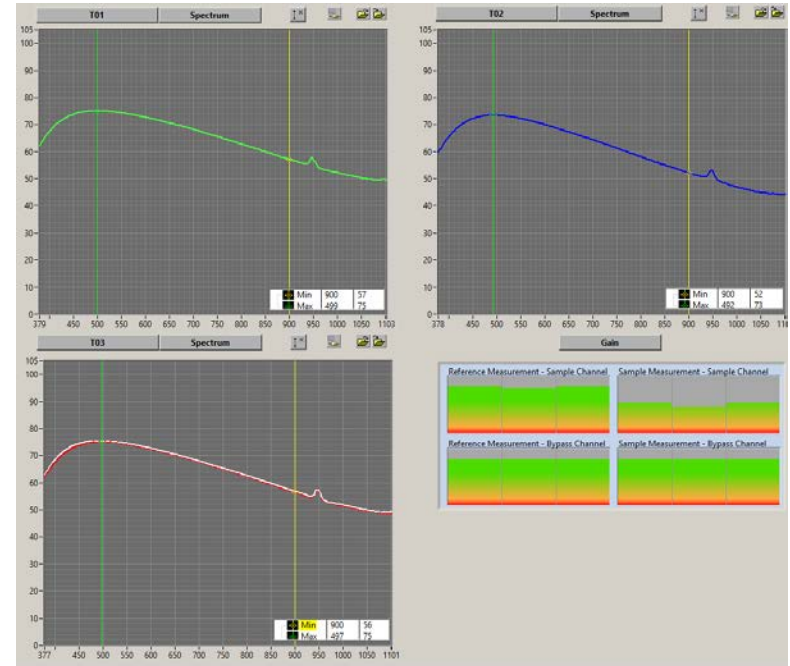


Industrial Roll to Roll fabrication of PV and LOW-E thin films



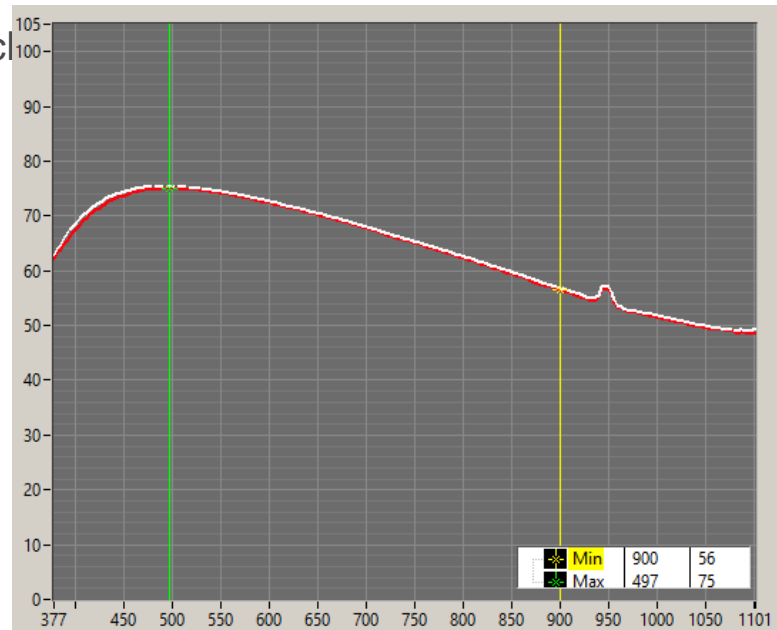
Results - Production stability

- ▲ Single Low-E test layer stack
- ▲ Transmittance 3 positions cross web
- ▲ Recorded after 4000m coating (green, blue red)
- ▲ White curve recorded at 150m



Results - Production stability

- Single Low-E test layer stack
- Transmittance
- 150m -> white curve
- 4000m -> red curve

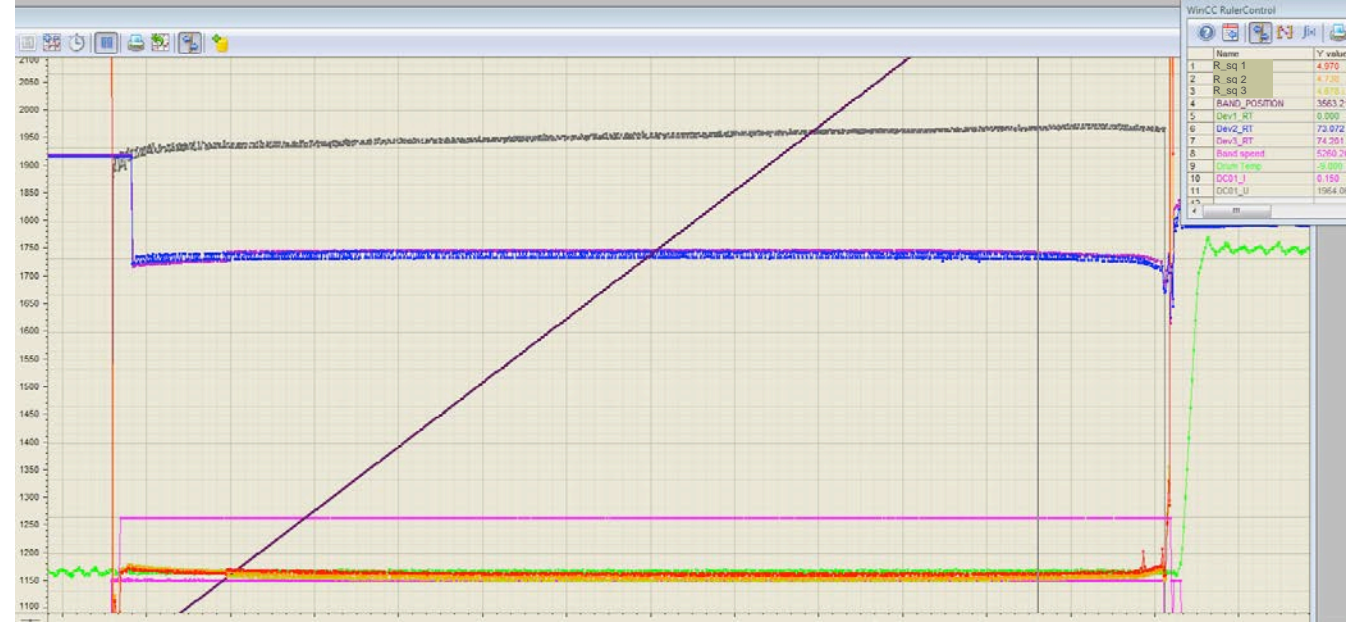


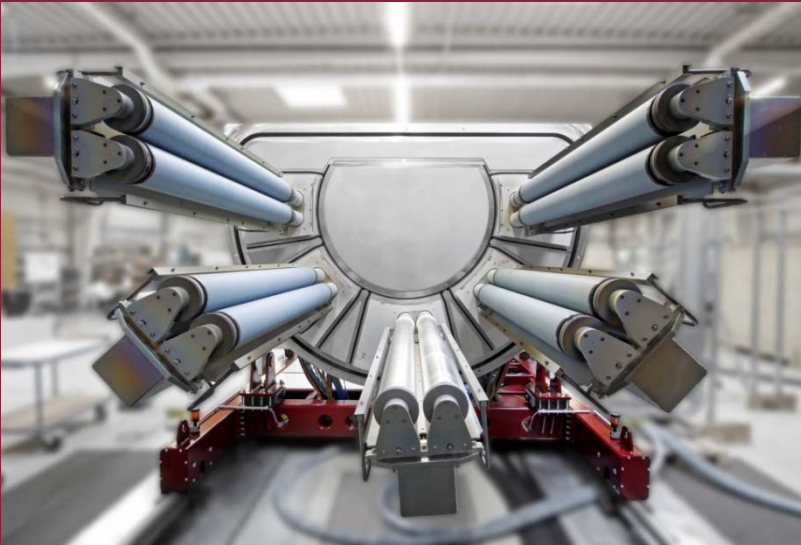
Industrial Roll to Roll fabrication of PV and LOW-E thin films



Results - Production stability

- Results LOW-E
- production stability
- Red, orange, yellow = Square resistance
- Blue, purple = Transmittance narrow spectral range approx 550nm.
- Diagram shows 4200m of production





www.fhr.de